

# Darlington Transistors

## NPN Silicon

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CES}$	30	Vdc
Collector–Base Voltage	$V_{CBO}$	30	Vdc
Emitter–Base Voltage	$V_{EBO}$	10	Vdc
Collector Current — Continuous	$I_C$	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

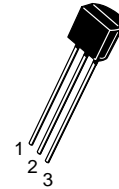
Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

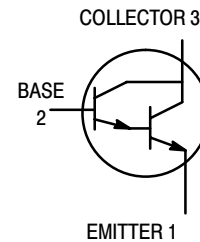
Collector–Emitter Breakdown Voltage ( $I_C = 100 \mu\text{Adc}$ , $I_B = 0$ )	$V_{(BR)CES}$	30	—	Vdc
Collector Cutoff Current ( $V_{CB} = 30 \text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	—	100	nAdc
Emitter Cutoff Current ( $V_{EB} = 10 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	—	100	nAdc

**MPSA13**  
**MPSA14\***

\*ON Semiconductor Preferred Device



**CASE 29-04, STYLE 1**  
**TO-92 (TO-226AA)**



Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# MPSA13 MPSA14

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS<sup>(1)</sup></b>				
DC Current Gain ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	MPSA13	5,000	—	—
	MPSA14	10,000	—	—
( $I_C = 100\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	MPSA13	10,000	—	—
	MPSA14	20,000	—	—
Collector–Emitter Saturation Voltage ( $I_C = 100\text{ mAdc}$ , $I_B = 0.1\text{ mAdc}$ )	$V_{CE(\text{sat})}$	—	1.5	Vdc
Base–Emitter On Voltage ( $I_C = 100\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$V_{BE(\text{on})}$	—	2.0	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product <sup>(2)</sup> ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	125	—	MHz

1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$ .
2.  $f_T = |h_{fe}| \cdot f_{\text{test}}$

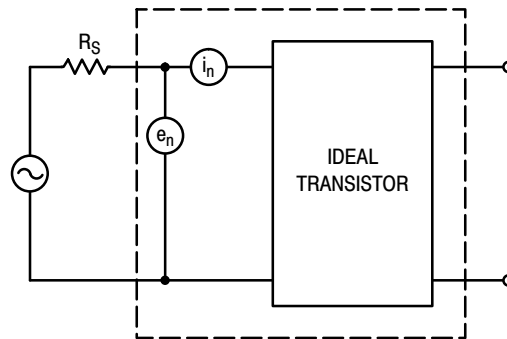


Figure 1. Transistor Noise Model

# MPSA13 MPSA14

## NOISE CHARACTERISTICS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

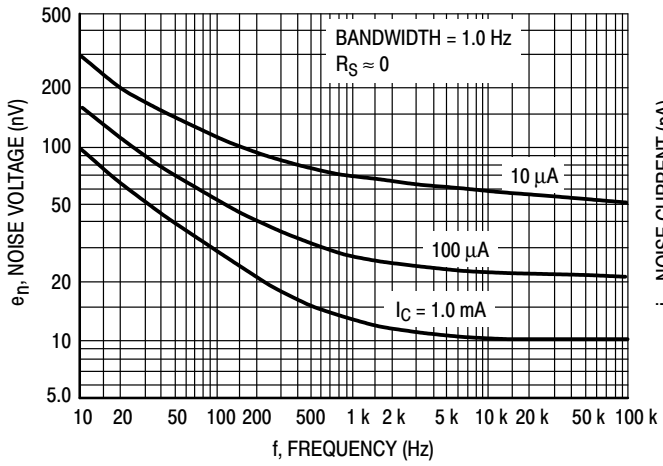


Figure 2. Noise Voltage

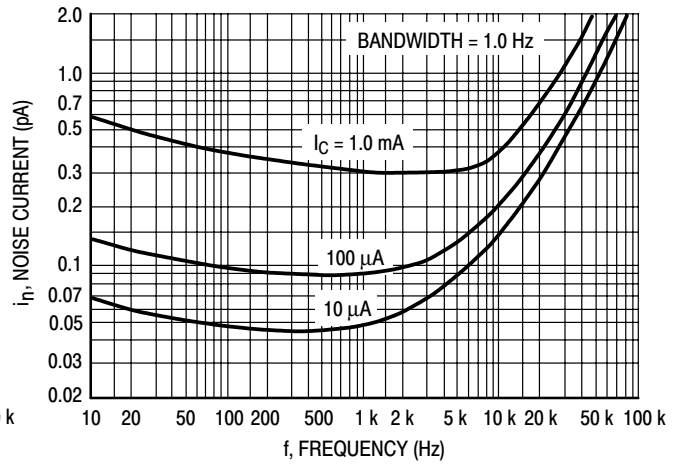


Figure 3. Noise Current

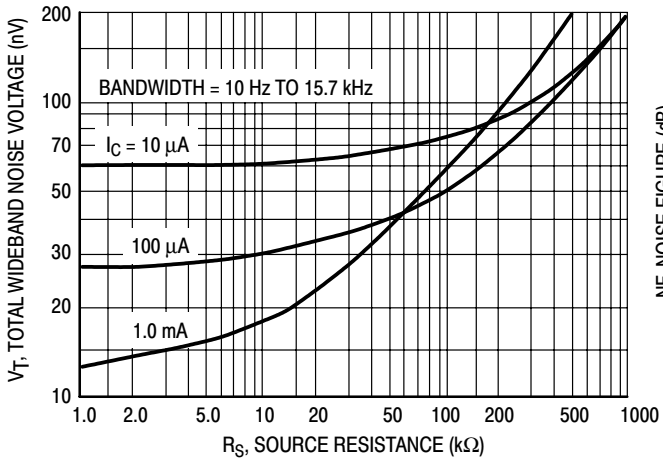


Figure 4. Total Wideband Noise Voltage

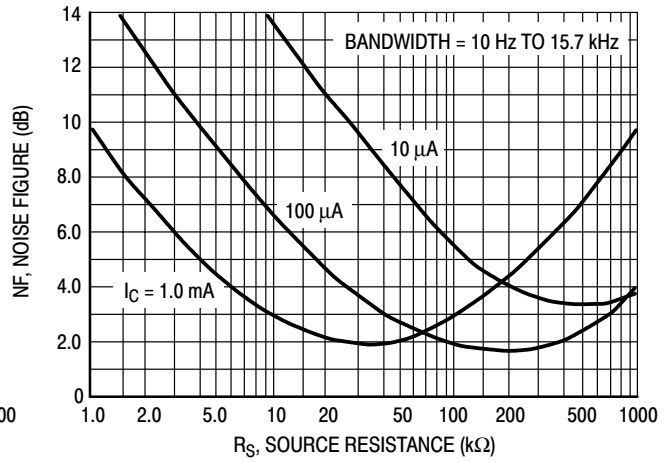


Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

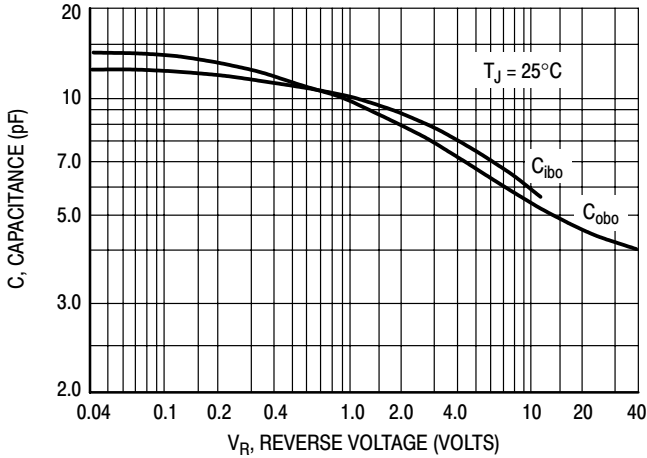


Figure 6. Capacitance

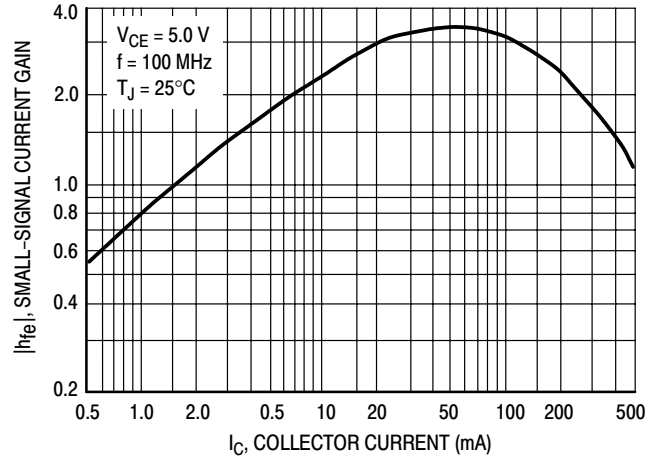


Figure 7. High Frequency Current Gain

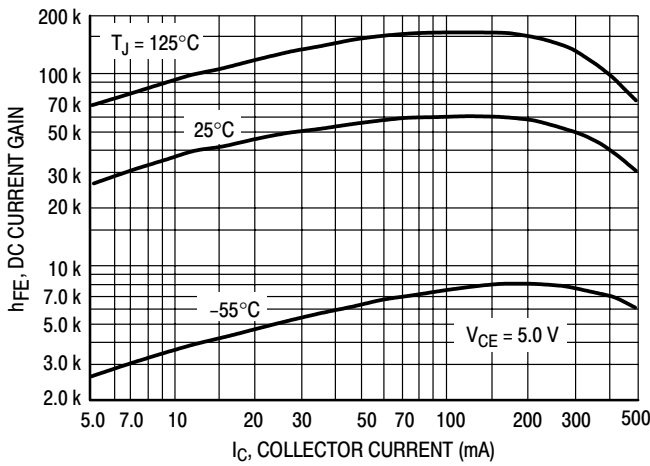


Figure 8. DC Current Gain

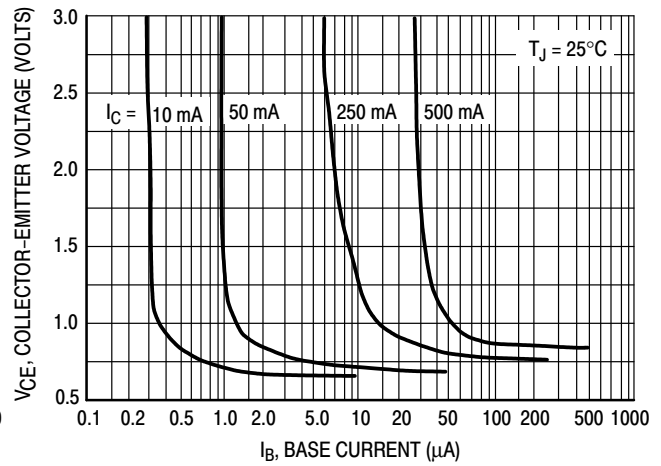


Figure 9. Collector Saturation Region

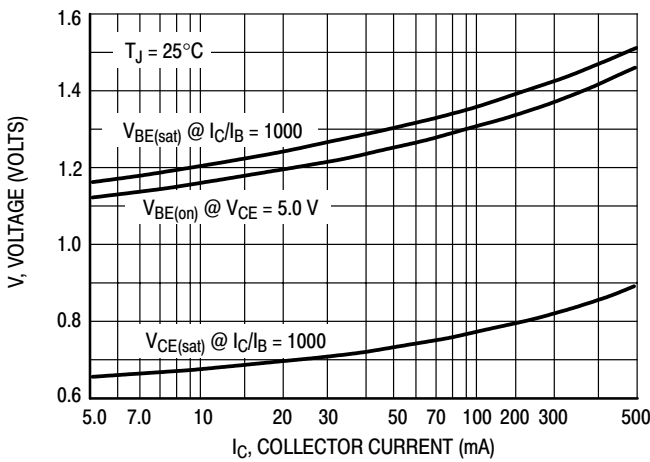


Figure 10. "On" Voltages

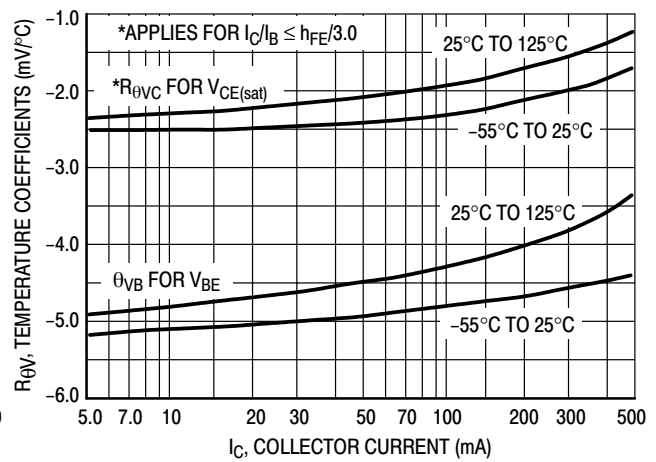


Figure 11. Temperature Coefficients

# MPSA13 MPSA14

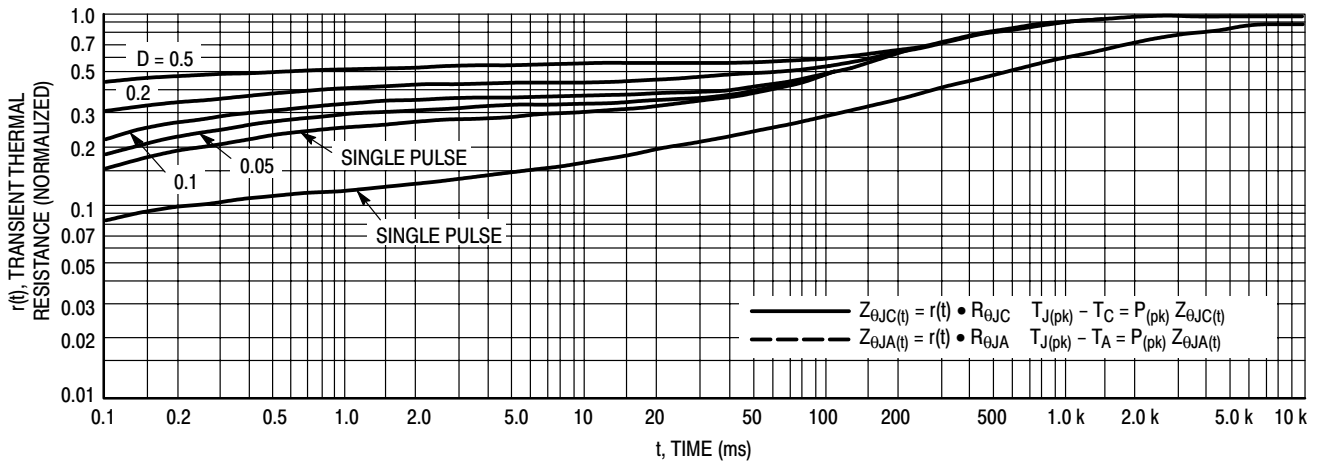


Figure 12. Thermal Response

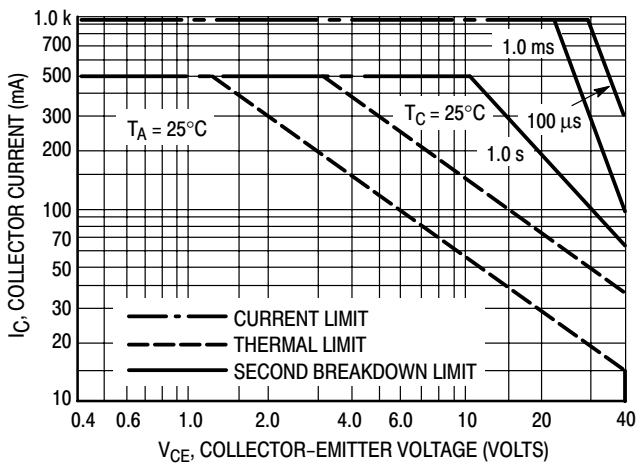
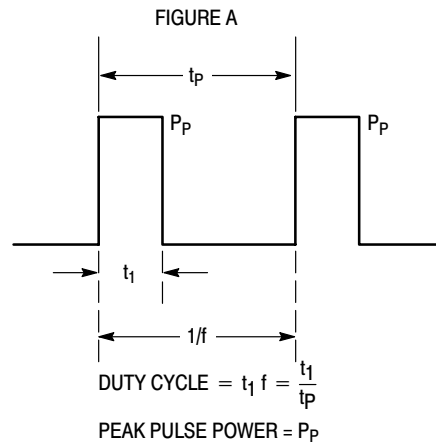


Figure 13. Active Region Safe Operating Area

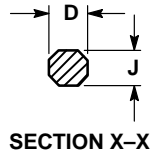
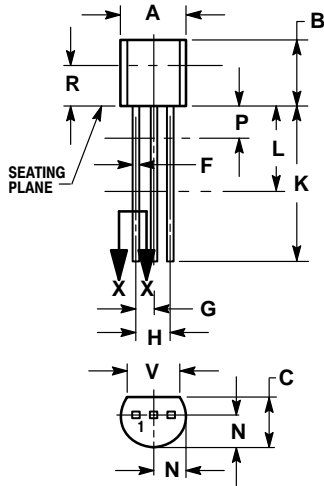


Design Note: Use of Transient Thermal Resistance Data

# MPSA13 MPSA14

## PACKAGE DIMENSIONS

CASE 029-04  
(TO-226AA)  
ISSUE AD



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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